

PBSS5250TH 50 V, 2 A PNP low VCEsat (BISS) transistor 9 August 2017

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- Higher efficiency leading to less heat genereation
- High temperature applications up to 175 °C
- AEC-Q101 qualified

3. Applications

- Power management
- DC-to-DC conversion
- Supply line switches
- · Battery charger switches
- · Peripheral drivers
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-50	V
I _C	collector current			-	-	-2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; T_{amb} = 25 °C	[1]	-	-	150	mΩ

[1] Pulse test: $t_p \le 300 \mu s$; $\delta \le 0.02$



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	C
2	Е	emitter		В
3	С	collector	1 2 TO-236AB (SOT23)	E sym132

6. Ordering information

Table 3. Ordering information

Type number	Package	e				
	Name	Description	Version			
PBSS5250TH	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5250TH	FH%

[1] % = placeholder for manufacturing site code

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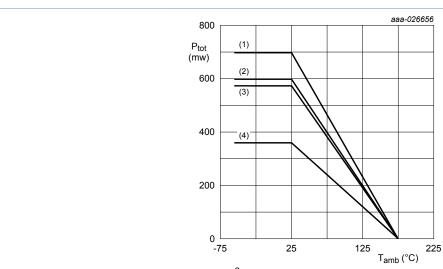
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-50	V
V_{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	Α
I _B	base current			-	-300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	360	mW
			[2]	-	575	mW
			[3]	-	600	mW
			[4]	-	700	mW
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, 4-layer copper, standard footprint
- (3) FR4 PCB, single sided copper, 1 cm²
- (4) FR4 PCB, single sided copper, standard footprint

Fig. 1. Power derating curves for SOT23

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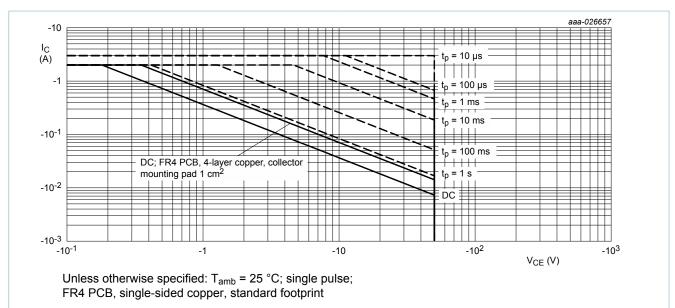


Fig. 2. Safe operating area; junction to ambient; continuous and peak drain currents as a function of collectoremitter voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	417	K/W
	from junction to ambient		[2]	-	-	261	K/W
			[3]	-	-	250	K/W
			[4]	-	-	215	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	75	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

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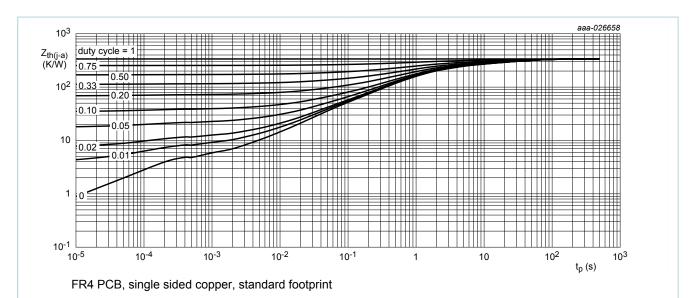


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

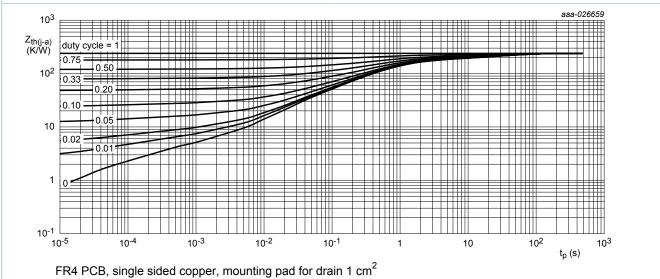


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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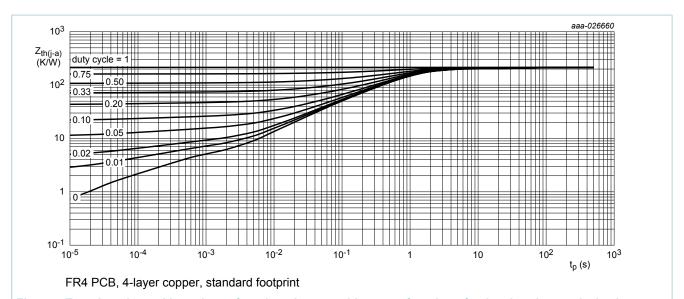


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

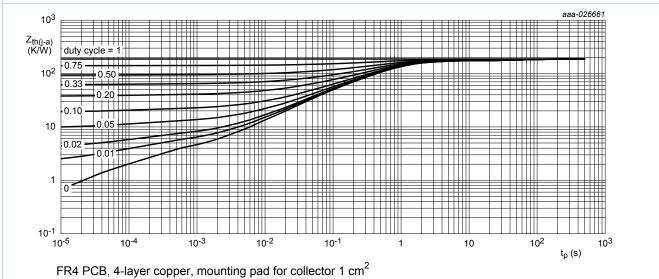


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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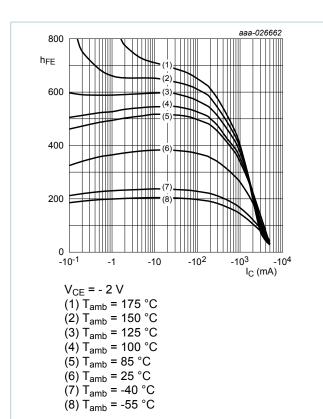
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I_C = -10 mA; I_B = 0 A; T_{amb} = 25 °C		-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_C = 0 \text{ mA}; I_E = -100 \mu\text{A}; T_{amb} = 25 ^{\circ}\text{C}$		-7	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-100	nA
	current	V _{CB} = -50 V; I _E = 0 A; T _j = 150 °C		-	-	-5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; T_{amb} = 25 °C	[1]	200	-	-	
		V_{CE} = -2 V; I_{C} = -500 mA; T_{amb} = 25 °C	[1]	200	-	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -1 \text{ A; } T_{amb} = 25 \text{ °C}$	[1]	200	-	-	
		V_{CE} = -2 V; I_{C} = -2 A; T_{amb} = 25 °C	[1]	130	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -500 mA; I_B = -50 mA; T_{amb} = 25 °C	[1]	-	-	-90	mV
		I_C = -1 A; I_B = -50 mA; T_{amb} = 25 °C	[1]	-	-	-180	mV
		I_C = -2 A; I_B = -200 mA; T_{amb} = 25 °C	[1]	-	-	-300	mV
R _{CEsat}	collector-emitter saturation resistance		[1]	-	-	150	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = -2 \text{ A}$; $I_B = -100 \text{ mA}$; $T_{amb} = 25 \text{ °C}$	[1]	-	-	-1.1	V
V_{BE}	base-emitter voltage	V _{CE} = -2 V; I _C = -1 A	[1]	-	-	-1.2	V
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C		100	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	35	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$

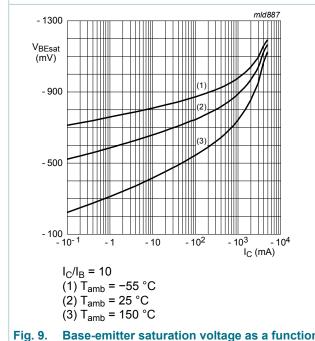
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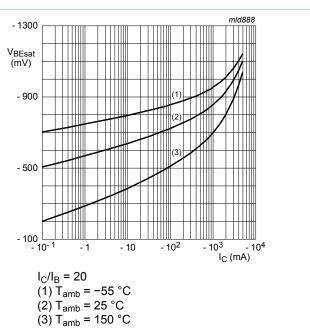
- 1200 V_{BE} (mV) - 800 - 400 - 10 -10^{2} I_C (mA) V_{CE} = −2 V (1) $T_{amb} = -55 \, ^{\circ}C$ (2) T_{amb} = 25 °C (3) $T_{amb} = 150 \, ^{\circ}C$

Base-emitter voltage as a function of collector Fig. 8. current; typical values





collector current; typical values



Base-emitter saturation voltage as a function of Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

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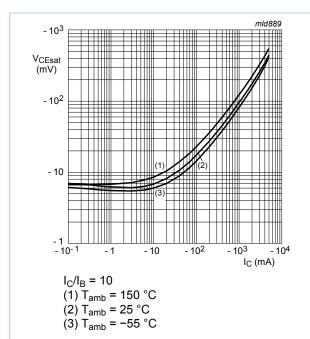


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

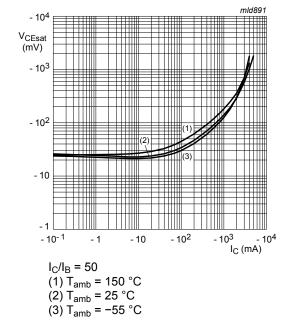


Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values

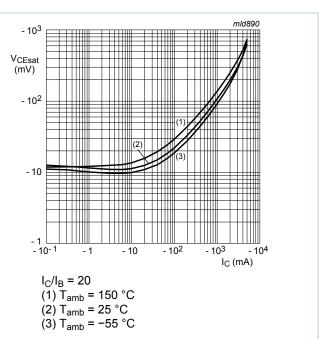


Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

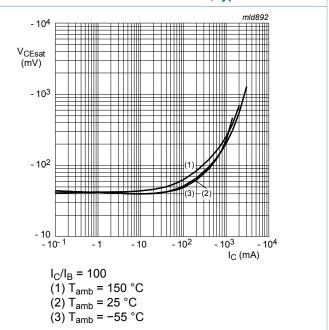
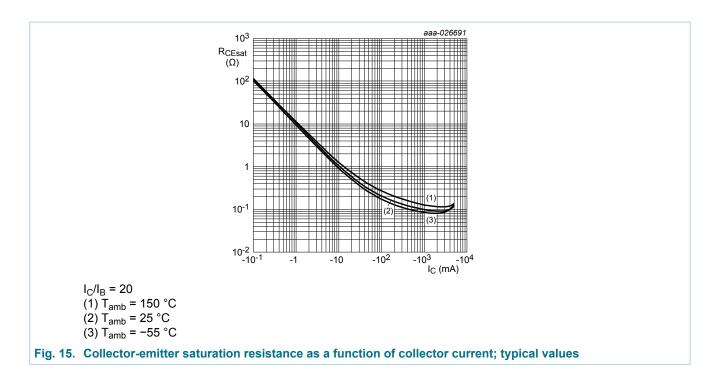


Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

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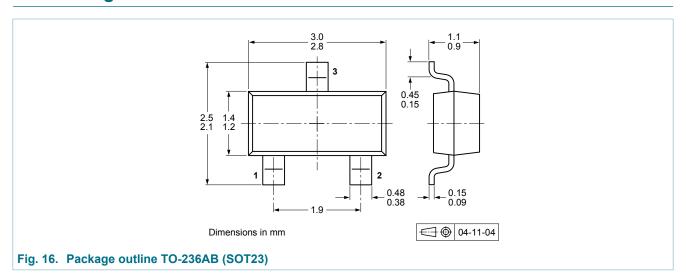


11. Test information

Quality information

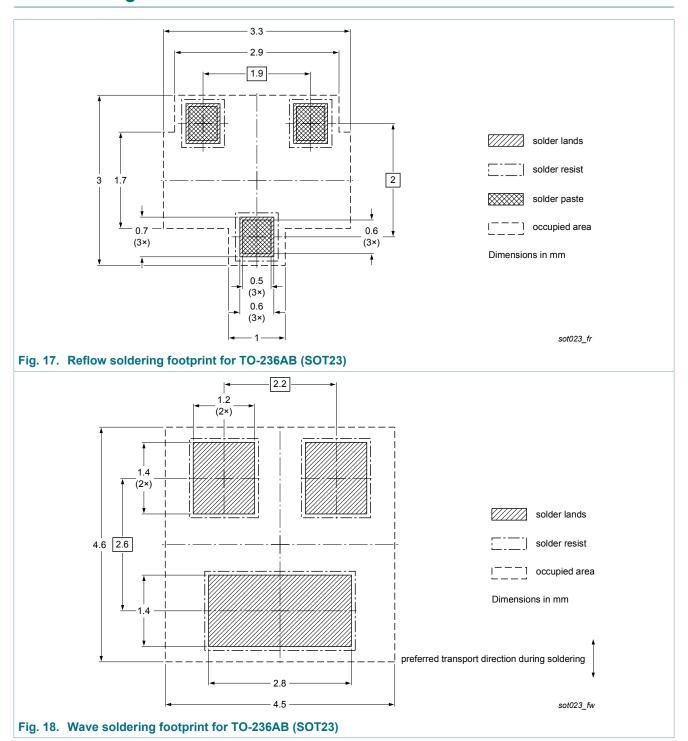
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS5250TH v.2	20170809	Product data sheet	-	PBSS5250TH v.1				
Modifications:	R _{th(j-sp)} maximum va	R _{th(j-sp)} maximum value revised to typical value						
PBSS5250TH v.1	20170421	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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